STARPOWER

SEMICONDUCTOR **IGBT**

GD75FFU120C6S

1200V/75A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction and switching loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS

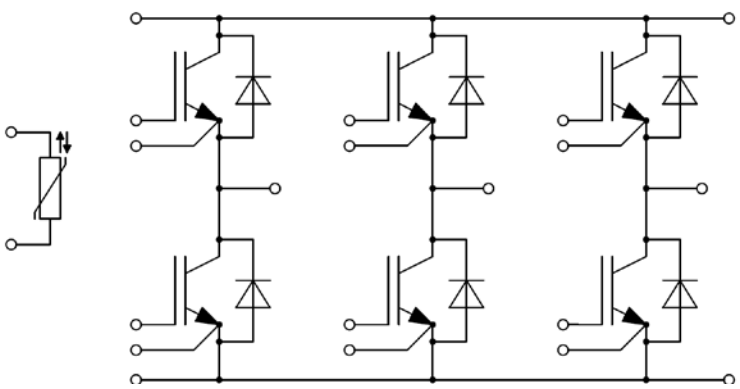
Features

- NPT IGBT technology
- 10μs short circuit capability
- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Square RBSOA
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25℃ unless otherwise noted

IGBT

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=25℃ @ T_C=80℃	115 75	A
I_{CM}	Pulsed Collector Current t_p=1ms	150	A
P_D	Maximum Power Dissipation @ T_j=150℃	667	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	150	A

Module

Symbol	Description	Values	Unit
T_{jmax}	Maximum Junction Temperature	150	℃
T_{jop}	Operating Junction Temperature	-40 to +125	℃
T_{STG}	Storage Temperature Range	-40 to +125	℃
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	4000	V

IGBT Characteristics T_C=25℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=75A,V_{GE}=15V, T_j=25℃		3.10	3.55	V
		I_C=75A,V_{GE}=15V, T_j=125℃		3.45		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=0.75mA,V_{CE}=V_{GE}, T_j=25℃	4.4	5.2	6.0	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25℃			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25℃			400	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	V_{CE}=30V,f=1MHz, V_{GE}=0V		6.35		nF
C_{res}	Reverse Transfer Capacitance			0.23		nF
Q_G	Gate Charge	V_{GE}=15V		600		nC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=75A, R_G=7.5Ω,V_{GE}=±15V, T_j=25℃		286		ns
t_r	Rise Time			53		ns
$t_{d(off)}$	Turn-Off Delay Time			304		ns
t_f	Fall Time			103		ns
E_{on}	Turn-On Switching Loss			4.16		mJ
E_{off}	Turn-Off Switching Loss			2.17		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=75A, R_G=7.5Ω,V_{GE}=±15V, T_j=125℃		297		ns
t_r	Rise Time			56		ns
$t_{d(off)}$	Turn-Off Delay Time			321		ns
t_f	Fall Time			136		ns
E_{on}	Turn-On Switching Loss			5.82		mJ
E_{off}	Turn-Off Switching Loss			3.44		mJ
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=125℃,V_{CC}=900V, V_{CEM}≤1200V		675		A

Diode Characteristics T_C=25℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_C=75A,V_{GE}=0V,T_j=25℃		1.75	2.20	V
		I_C=75A,V_{GE}=0V,T_j=125℃		1.85		
Q_r	Recovered Charge	V_R=600V,I_F=75A, R_G=7.5Ω,V_{GE}=-15V T_j=25℃		3.6		μC
I_{RM}	Peak Reverse Recovery Current			63		A
E_{rec}	Reverse Recovery Energy			2.21		mJ
Q_r	Recovered Charge	V_R=600V,I_F=75A, R_G=7.5Ω,V_{GE}=-15V T_j=125℃		7.9		μC
I_{RM}	Peak Reverse Recovery Current			73		A
E_{rec}	Reverse Recovery Energy			4.48		mJ

NTC Characteristics T_C=25℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100℃,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

Module Characteristics T_C=25℃ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		21		nH
$R_{CC'+EE'}$	Module Lead Resistance,Terminal to Chip		1.80		mΩ
$R_{\theta JC}$	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.225 0.370	K/W
$R_{\theta CS}$	Case-to-Sink (per IGBT) Case-to-Sink (per Diode)		0.193 0.317		K/W
$R_{\theta CS}$	Case-to-Sink		0.009		K/W
M	Mounting Torque, Screw M5	3.0		6.0	N.m
G	Weight of Module		300		g

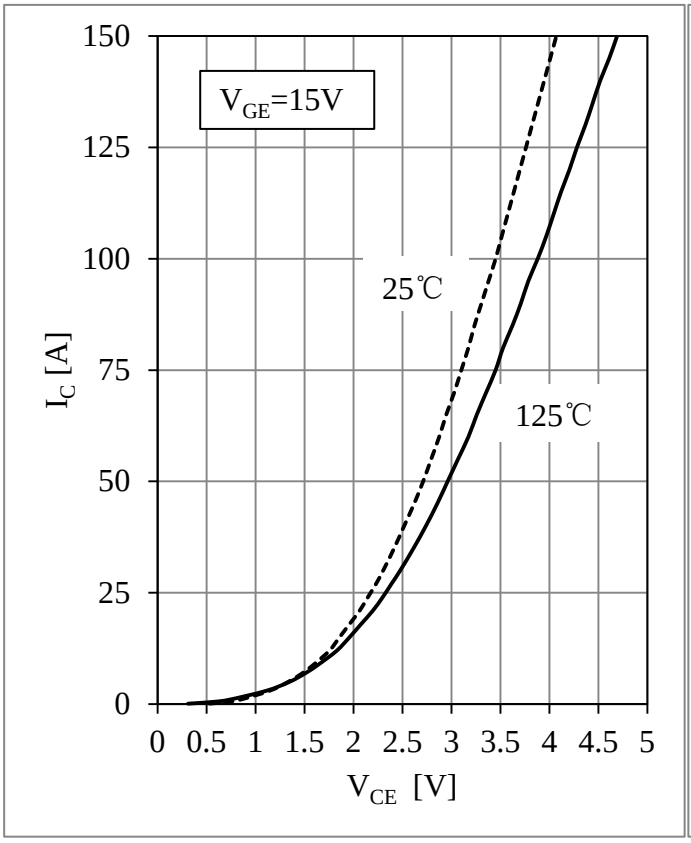


Fig 1. IGBT Output Characteristics

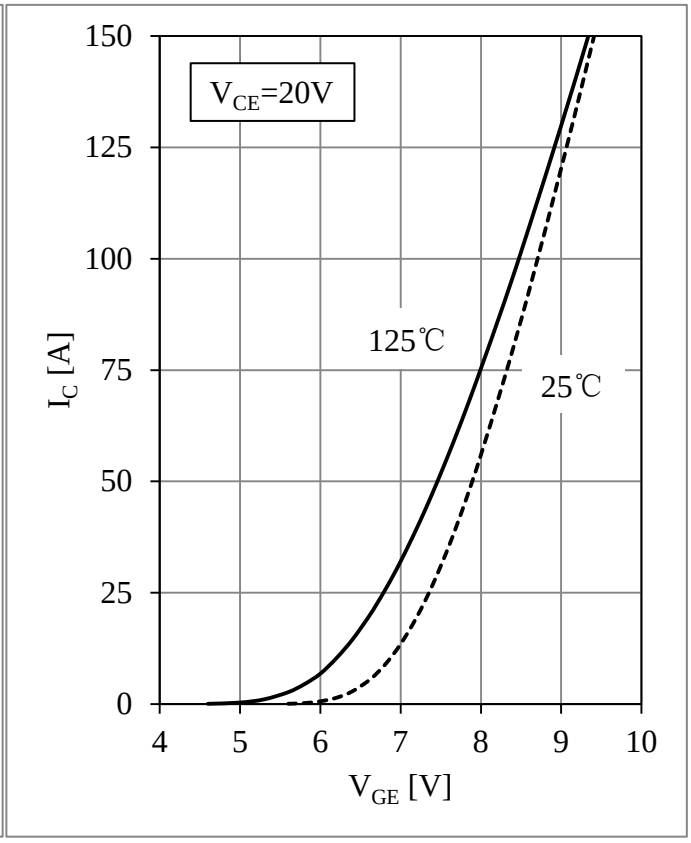


Fig 2. IGBT Transfer Characteristics

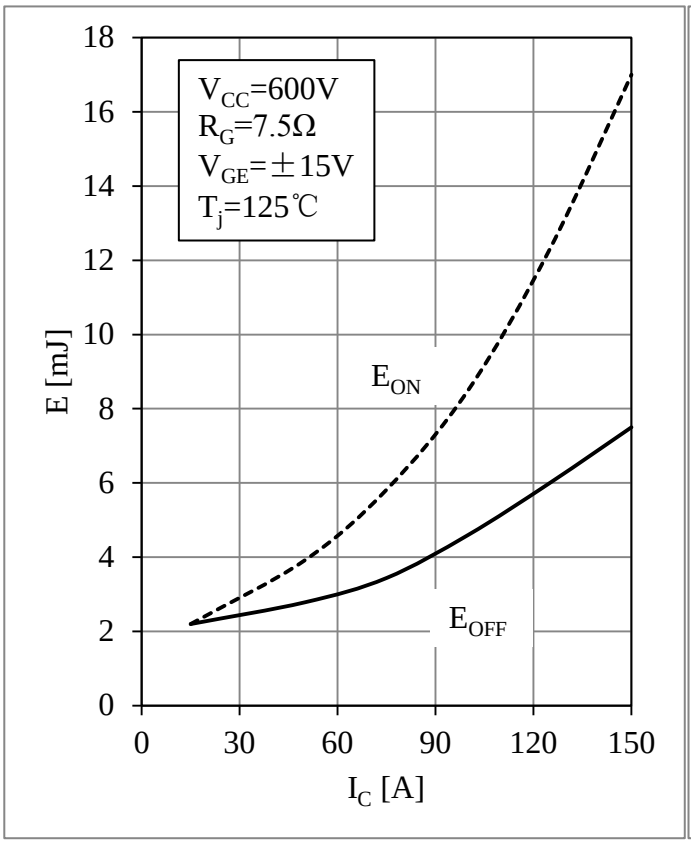


Fig 3. IGBT Switching Loss vs. I_C

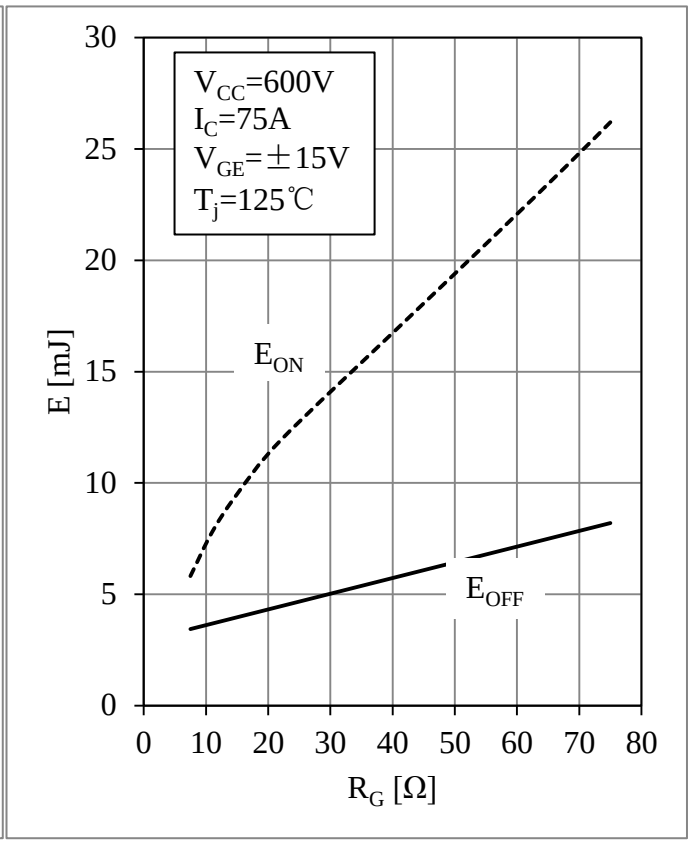


Fig 4. IGBT Switching Loss vs. R_G

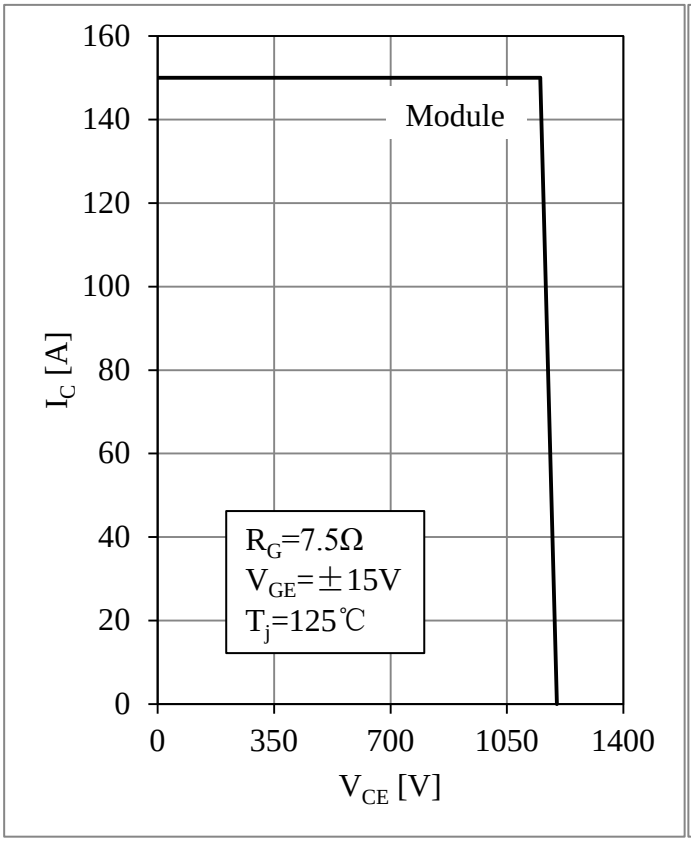


Fig 5. RBSOA

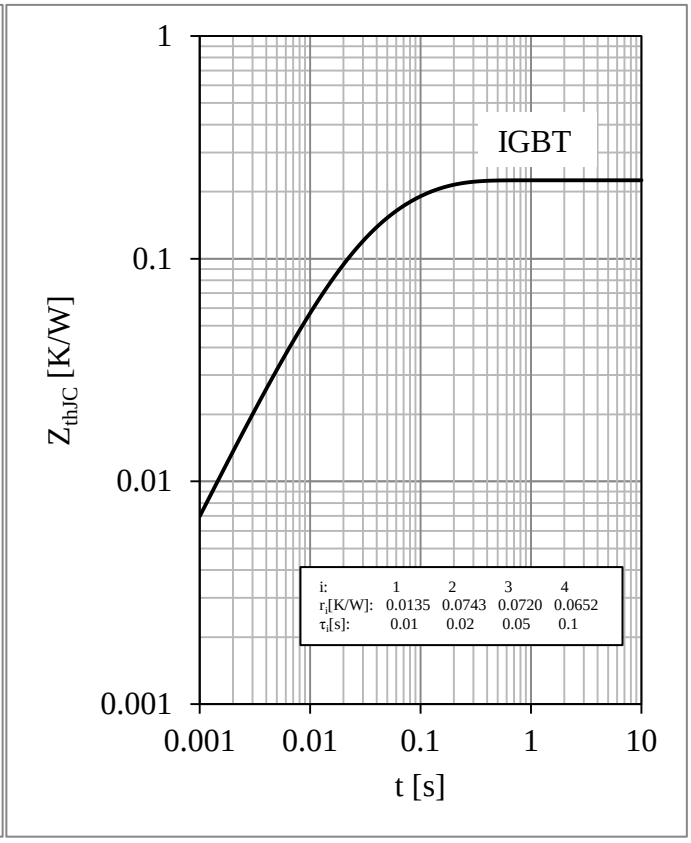


Fig 6. IGBT Transient Thermal Impedance

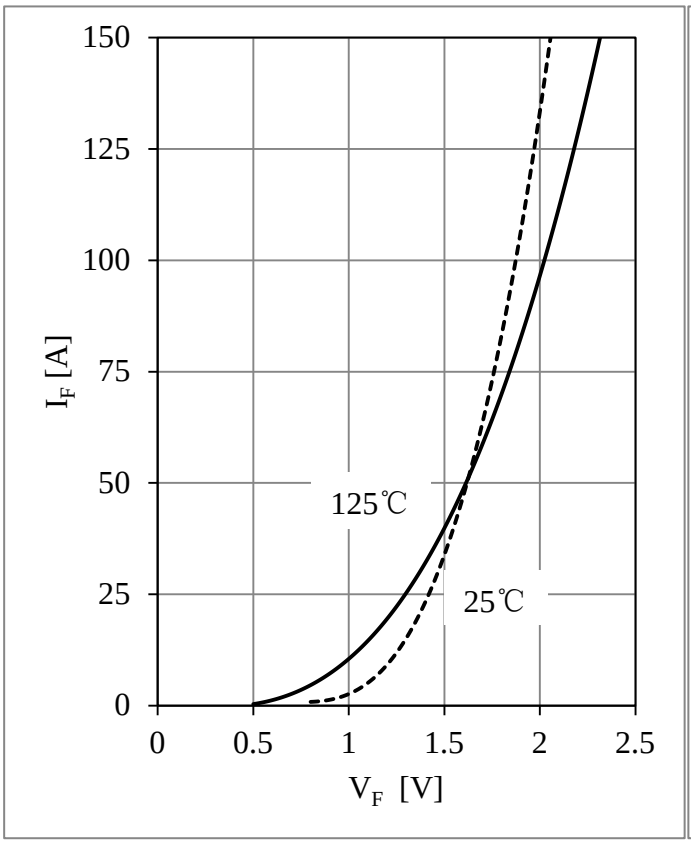


Fig 7. Diode Forward Characteristics

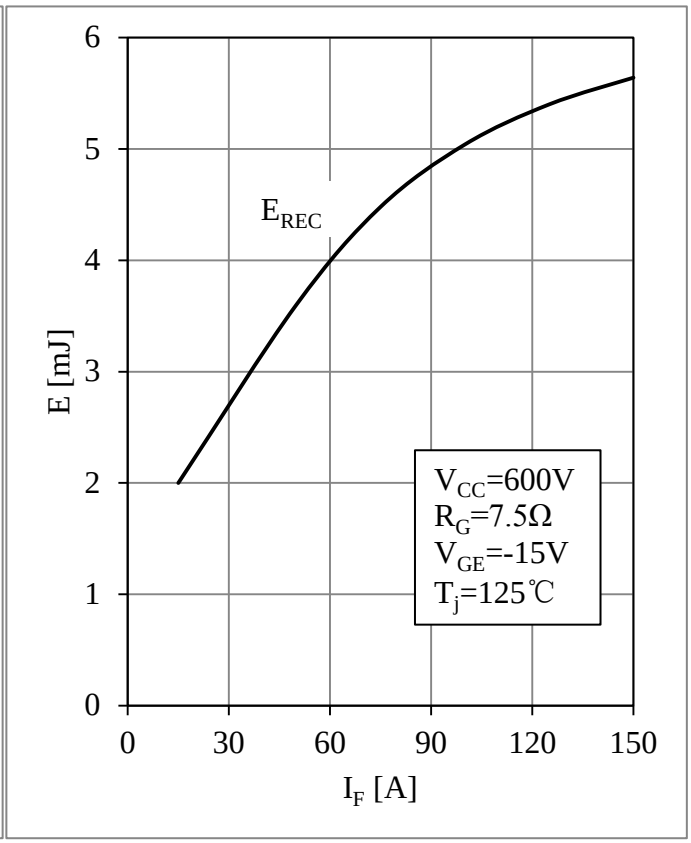


Fig 8. Diode Switching Loss vs. I_F

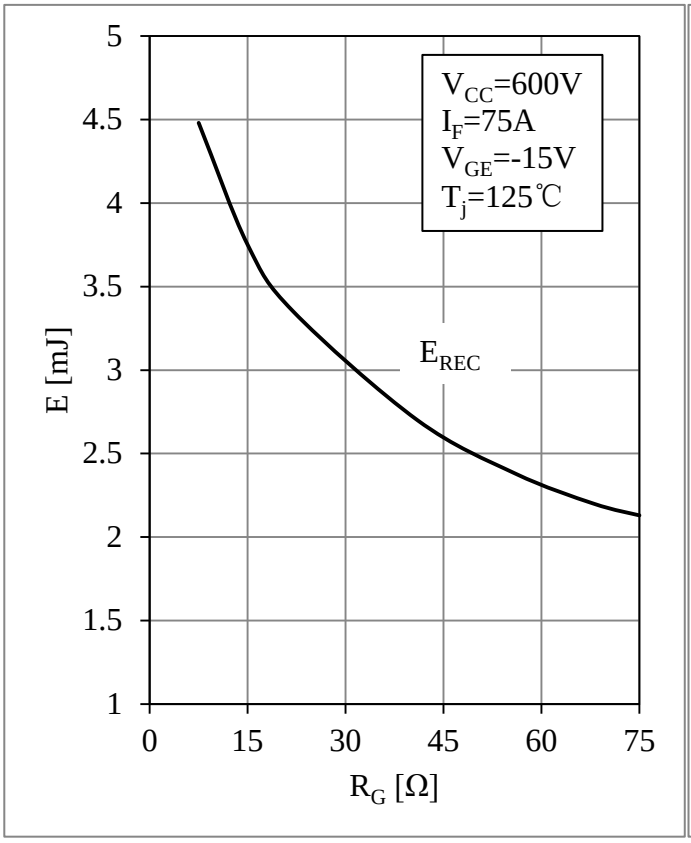


Fig 9. Diode Switching Loss vs. R_G

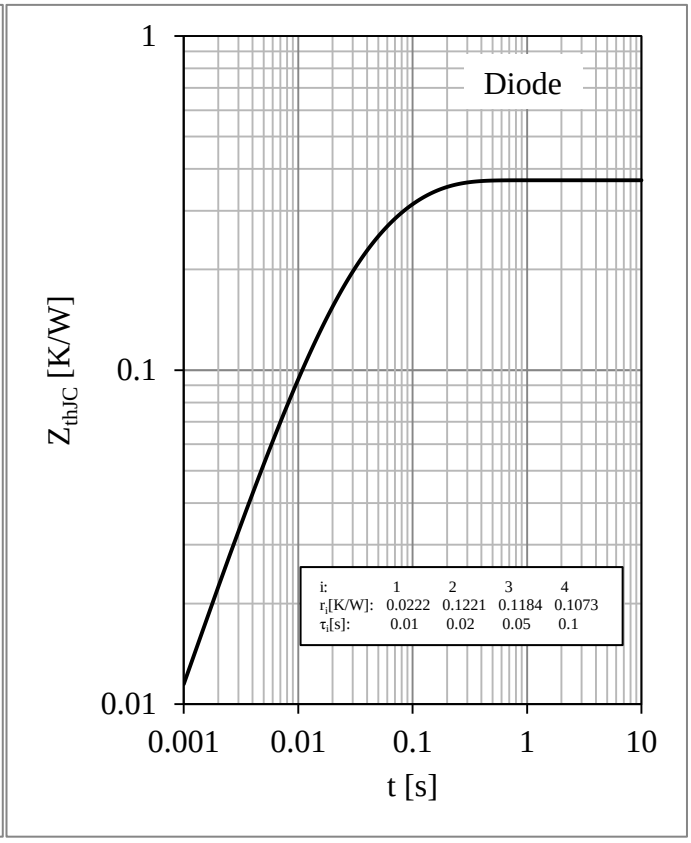


Fig 10. Diode Transient Thermal Impedance

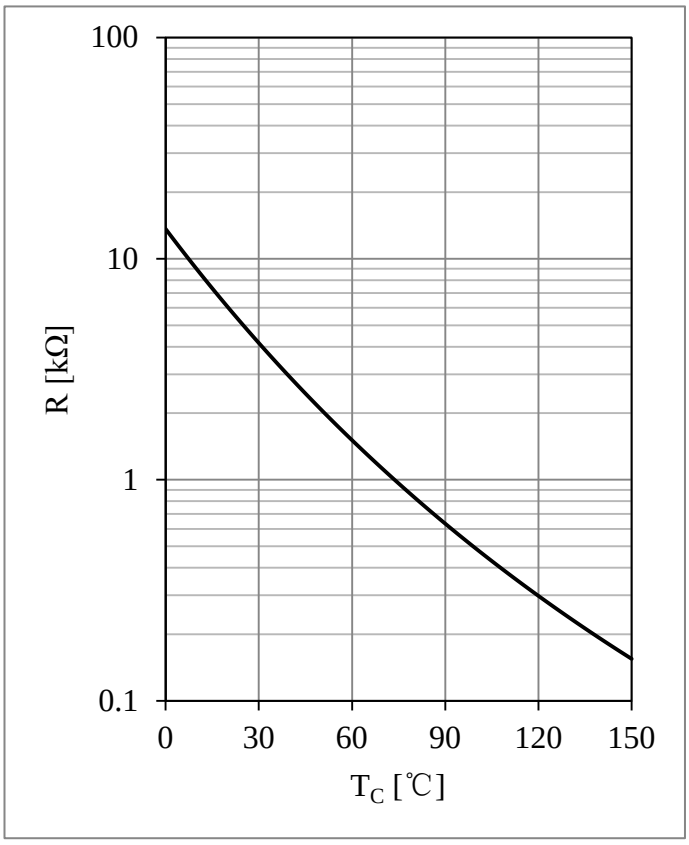
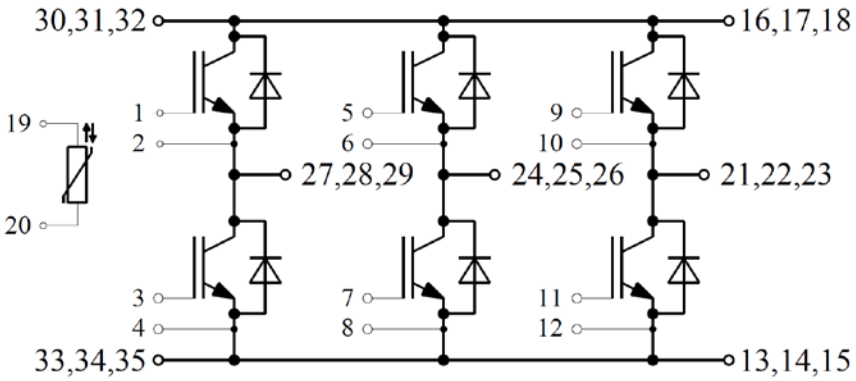


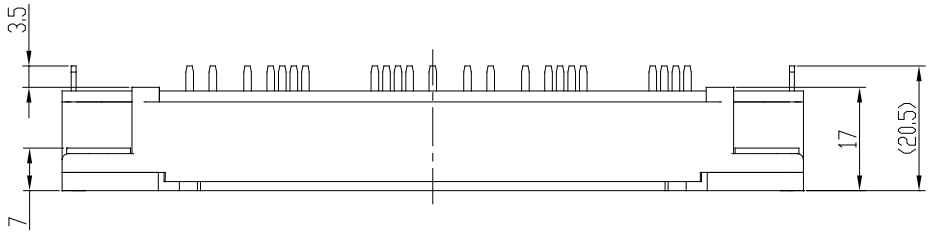
Fig 11. NTC Temperature Characteristic

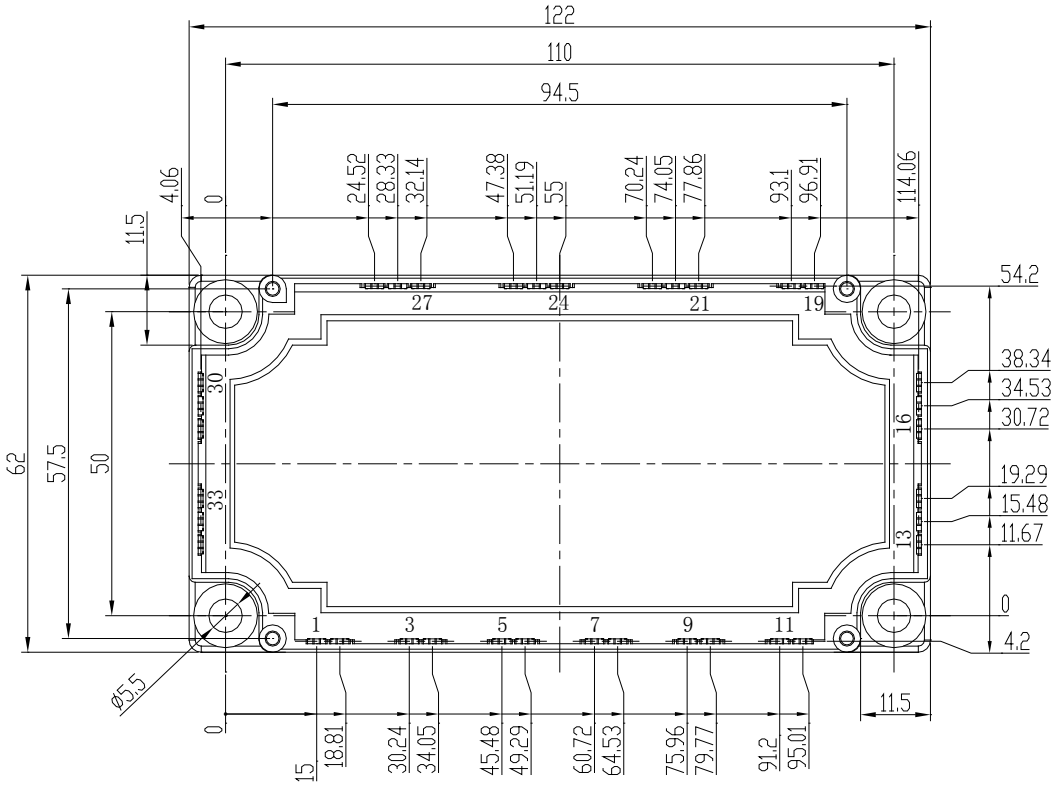
Circuit Schematic



Package Dimensions

Dimensions in Millimeters





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